Abstracts

A Silicon BiCMOS Transceiver Front-End MMIC Covering 900 and 1900 MHz Applications

W. Titus, M. Shifrin, V. Aparin and B. Bedard. "A Silicon BiCMOS Transceiver Front-End MMIC Covering 900 and 1900 MHz Applications." 1996 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 98. (1996 [MCS]): 73-76.

A Silicon BiCMOS transceiver front-end consisting of a low noise amplifier, power amplifier, and SPDT switch is described. The chip runs off a 5 V supply and requires a single CMOS/TTL control line for switch control. The LNA path has a 22 dB gain and 4 dB noise figure at 900 MHz. The PA has a gain of 22 dB and a output power of 15 dBm. The SPDT switch has an insertion loss of 1.3 dB, and an isolation of 22 dB at 900 MHz.

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